Octal 3-State Inverting Buffer/Line Driver/Line Receiver

High-Performance Silicon-Gate CMOS

The MC74HC540A is identical in pinout to the LS540. The device inputs are compatible with Standard CMOS outputs. External pull–up resistors make them compatible with LSTTL outputs.

The HC540A is an octal inverting buffer/line driver/line receiver designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. This device features inputs and outputs on opposite sides of the package and two ANDed active-low output enables.

The HC540A is similar in function to the HC541A, which has noninverting outputs.

Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance With the JEDEC Standard No. 7 A Requirements
- Chip Complexity: 124 FETs or 31 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

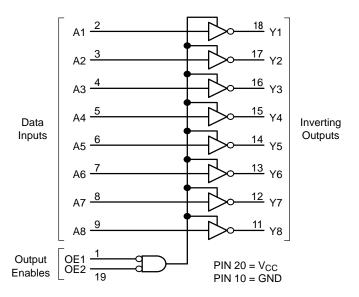


Figure 1. Logic Diagram



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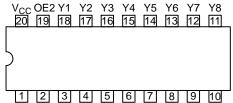
CASE 751D





DT SUFFIX CASE 948E

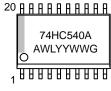
PIN ASSIGNMENT

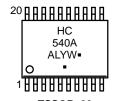


OE1 A1 A2 A3 A4 A5 A6 A7 A8 GND

20-Lead (Top View)

MARKING DIAGRAMS





SOIC-20

TSSOP-20

A = Assembly Location WL, L = Wafer Lot

WL, L = Water Lot YY, Y = Year WW, W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

FUNCTION TABLE

	Inputs	Output V	
OE1	OE2	Α	Output Y
L	L	L	Н
L	L	Н	L
Н	Х	Х	Z
X	Н	Х	Z

Z = High Impedance X = Don't Care

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS

Symbol	F	Value	Unit	
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
VI	DC Input Voltage		–0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage (Note 1)		$-0.5 \le V_{O} \le V_{CC} + 0.5$	V
I _{IK}	DC Input Diode Current		±20	mA
I _{OK}	DC Output Diode Current		±35	mA
Io	DC Output Sink Current		±35	mA
I _{CC}	DC Supply Current per Supply Pin		±75	mA
I _{GND}	DC Ground Current per Ground Pin		±75	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
T _L	Lead Temperature, 1 mm from Case f	for 10 Seconds	260	°C
TJ	Junction Temperature Under Bias		+150	°C
$\theta_{\sf JA}$	Thermal Resistance	SOIC TSSOP	96 128	°C/W
P _D	Power Dissipation in Still Air at 85°C	SOIC TSSOP	500 450	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 30% – 35%	UL 94 V0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 > 1000	V
I _{LATCHUP}	Latchup Performance	Above V _{CC} and Below GND at 85°C (Note 5)	±300	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. I_O absolute maximum rating must be observed.
- Tested to EIA/JESD22-A114-A.
 Tested to EIA/JESD22-A115-A.
- 4. Tested to JESD22-C101-A.
- 5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	DC Supply Voltage	(Referenced to GND)	2.0	6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage	(Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types		-55	+125	°C
t _r , t _f	Input Rise and Fall Time (Figure 3)	$V_{CC} = 2.0 \text{ V}$ $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 0 0	1000 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

6. Unused inputs may not be left open. All inputs must be tied to a high- or low-logic input voltage level.

DC CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Condition	V _{CC}	–55 to 25°C	≤85°C	≤125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	V
V _{IL}	Maximum Low–Level Input Voltage	$\begin{aligned} V_{out} &= V_{CC} - 0.1 \text{ V} \\ I_{out} &\leq 20 \mu\text{A} \end{aligned}$	2.0 3.0 4.5 6.0	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IL}$ $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$\begin{split} V_{in} = V_{IL} & I_{out} \leq 3.6 \text{ mA} \\ & I_{out} \leq 6.0 \text{ mA} \\ & I_{out} \leq 7.8 \text{ mA} \end{split}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
V _{OL}	Maximum Low–Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	\ \
		$\begin{split} V_{in} = V_{IH} & I_{out} \leq 3.6 \text{ mA} \\ I_{out} \leq 6.0 \text{ mA} \\ I_{out} \leq 7.8 \text{ mA} \end{split}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	±0.1	±1.0	±1.0	μΑ
I _{OZ}	Maximum Three–State Leakage Current	Output in High Impedance State $V_{in} = V_{IL}$ or V_{IH} $V_{out} = V_{CC}$ or GND	6.0	±0.5	±5.0	±10.0	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4	40	160	μА

AC CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

			Gu	aranteed Li	mit	
Symbol	Parameter	V _{CC}	–55 to 25°C	≤85°C	≤125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 2 and 4)	2.0 3.0 4.5 6.0	80 30 18 15	100 40 23 20	120 55 28 25	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Output Enable to Output Y (Figures 3 and 5)	2.0 3.0 4.5 6.0	110 45 25 21	140 60 31 26	165 75 38 31	ns
t _{PZL} , t _{PZH}	Maximum Propagation Delay, Output Enable to Output Y (Figures 3 and 5)	2.0 3.0 4.5 6.0	110 45 25 21	140 60 31 26	165 75 38 31	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 2 and 4)	2.0 3.0 4.5 6.0	60 22 12 10	75 28 15 13	90 34 18 15	ns
C _{in}	Maximum Input Capacitance		10	10	10	pF
C _{out}	Maximum 3-State Output Capacitance (Output in High Impedance State)		15	15	15	pF

		Typical @ 25°C, $V_{CC} = 5.0 \text{ V}, V_{EE} = 0 \text{ V}$	
C_{PD}	Power Dissipation Capacitance (Per Buffer) (Note 7)	35	pF

^{7.} Used to determine the no–load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

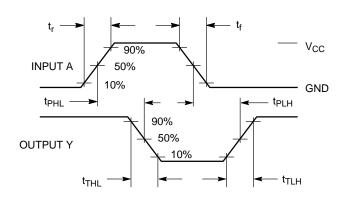


Figure 2. Switching Waveform

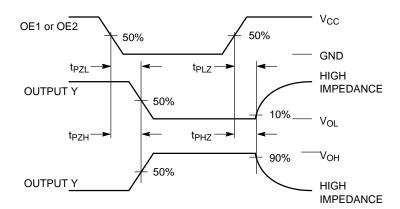
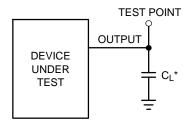
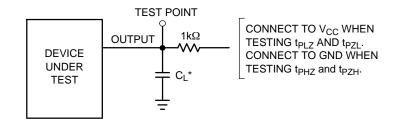


Figure 3. Switching Waveform



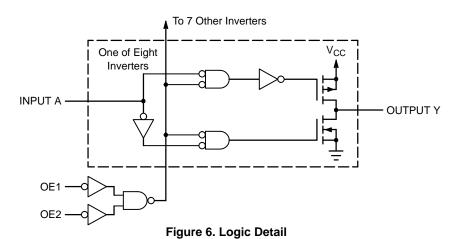
*Includes all probe and jig capacitance

Figure 4. Test Circuit



*Includes all probe and jig capacitance

Figure 5. Test Circuit



PIN DESCRIPTIONS

INPUTS

A1, A2, A3, A4, A5, A6, A7, A8 (PINS 2, 3, 4, 5, 6, 7, 8, 9)

Data input pins. Data on these pins appear in inverted form on the corresponding Y outputs, when the outputs are enabled.

CONTROLS

OE1, OE2 (PINS 1, 19)

Output enables (active-low). When a low voltage is applied to both of these pins, the outputs are enabled and the

device functions as an inverter. When a high voltage is applied to either input, the outputs assume the high impedance state.

OUTPUTS

Y1, Y2, Y3, Y4, Y5, Y6, Y7, Y8 (PINS 18, 17, 16, 15, 14, 13, 12, 11)

Device outputs. Depending upon the state of the output enable pins, these outputs are either inverting outputs or high-impedance outputs.

ORDERING INFORMATION

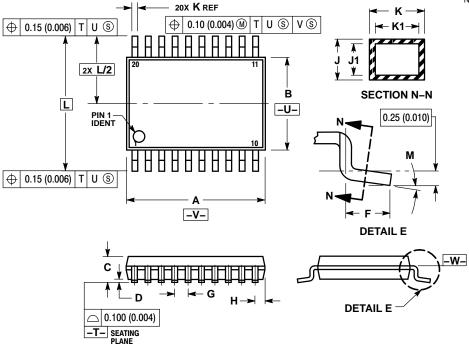
Device	Package	Shipping [†]
MC74HC540ADWG	SOIC-20 WIDE (Pb-Free)	38 Units / Rail
MC74HC540ADWR2G	SOIC-20 WIDE (Pb-Free)	1000 Tape & Reel
MC74HC540ADTR2G	TSSOP-20 (Pb-Free)	2500 Tape & Reel
NLV74HC540ADTR2G*	TSSOP-20 (Pb-Free)	2500 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable

PACKAGE DIMENSIONS

TSSOP-20 **DT SUFFIX** CASE 948E-02 ISSUE C



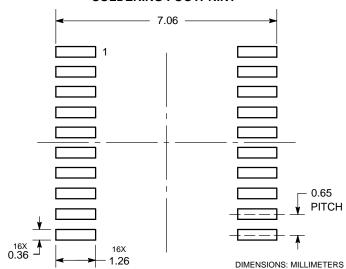
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION:
 MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.

 - INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION.
 SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE
 DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.08
 (0.003) TOTAL IN EXCESS OF THE K
 DIMENSION AT MAXIMUM MATERIAL
 CONDITION.

 - CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40		0.252	BSC
M	0°	8°	0°	8°

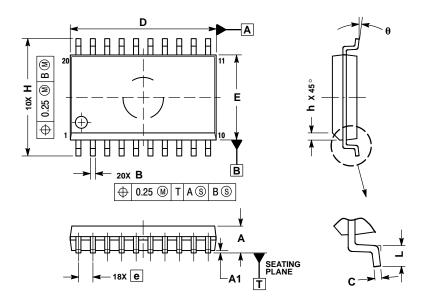
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOIC-20 DW SUFFIX CASE 751D-05 ISSUE G



NOTES:

- DIMENSIONS ARE IN MILLIMETERS.
- INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- MAXIMUM MOLD FROTROSION 1.15 FE 339
 DIMENSION B DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE PROTRUSION
 SHALL BE 0.13 TOTAL IN EXCESS OF B
 DIMENSION AT MAXIMUM MATERIAL
 CONDITION.

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.35	2.65	
A1	0.10	0.25	
В	0.35	0.49	
C	0.23	0.32	
D	12.65	12.95	
E	7.40	7.60	
е	1.27	BSC	
Н	10.05	10.55	
h	0.25	0.75	
L	0.50	0.90	
θ	0°	7 °	

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